

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-5 (Canceled).

Claim 6 (New): A ceramic heater having a ceramic substrate with a conductor inside of the ceramic substrate,

wherein said ceramic substrate is sintered and has a fractured section thereof having intergranular fracture.

Claim 7 (New): The ceramic heater according to claim 6,
wherein an average diameter of ceramic grains of said fractured section is 0.5 to 10 μm .

Claim 8 (New): The ceramic heater according to claim 6,
wherein an impurity element is locally distributed in boundaries of ceramic grains of said fractured section.

Claim 9 (New): The ceramic heater according to claim 6,
wherein the thermal conductivity of said ceramic substrate is 100 W/m•K or more.

Claim 10 (New): The ceramic heater according to claim 6,
wherein said ceramic substrate has a diameter of 200 mm or more.

Claim 11 (New): The ceramic heater according to claim 6,
wherein said ceramic substrate has a diameter of 300 mm or more.

Claim 12 (New): The ceramic heater according to claim 6,
wherein said ceramic substrate has a thickness of 25 mm or less.

Claim 13 (New): The ceramic heater according to claim 8,
wherein said impurity element is selected from the group consisting of boron, sodium,
calcium, silicon and a sintering aid.

Claim 14 (New): The ceramic heater according to claim 8,
wherein said impurity element is selected from the group consisting of Si, Y and O.

Claim 15 (New): The ceramic heater according to claim 6, wherein said ceramic
substrate has
an impurity-existent area where an impurity element is locally distributed in triple
points of crystal grains, and
an impurity element-nonexistent area where an impurity is not locally distributed in
the triple points of the crystal grains.

Claim 16 (New): The ceramic heater according to claim 15,
wherein said impurity element is selected from the group consisting of boron, sodium,
calcium, silicon and a sintering aid.

Claim 17 (New): The ceramic heater according to claim 15,
wherein said impurity element is selected from the group consisting of Si, Y and O.

Claim 18 (New): The ceramic heater according to claim 6,
wherein said ceramic substrate comprises a nitride ceramic, a carbide ceramic or an
oxide ceramic.

Claim 19 (New): The ceramic heater according to claim 6,
wherein said ceramic substrate comprises aluminum nitride or silicon carbide.

Claim 20 (New): The ceramic heater according to claim 6,
wherein said ceramic heater is capable of use at a temperature of 150°C to 200°C.

Claim 21 (New): A semiconductor producing/examining device comprising the
ceramic heater claimed in Claim 6.

Claim 22 (New): A ceramic heater having a ceramic substrate with a conductor on a
surface of the ceramic substrate,
wherein said ceramic substrate is sintered and has a fractured section thereof having
intergranular fracture.

Claim 23 (New): The ceramic heater according to claim 22,
wherein an average diameter of ceramic grains of said fractured section is 0.5 to 10
μm.

Claim 24 (New): The ceramic heater according to claim 22,
wherein an impurity element is locally distributed in boundaries of ceramic grains of
said fractured section.

Claim 25 (New): The ceramic heater according to claim 22,
wherein the thermal conductivity of said ceramic substrate is 100 W/m•K or more.

Claim 26 (New): The ceramic heater according to claim 22,
wherein said ceramic substrate has a diameter of 200 mm or more.

Claim 27 (New): The ceramic heater according to claim 22,
wherein said ceramic substrate has a diameter of 300 mm or more.

Claim 28 (New): The ceramic heater according to claim 22,
wherein said ceramic substrate has a thickness of 25 mm or less.

Claim 29 (New): The ceramic heater according to claim 24,
wherein said impurity element is selected from the group consisting of boron, sodium,
calcium, silicon and a sintering aid.

Claim 30 (New): The ceramic heater according to claim 24,
wherein said impurity element is selected from the group consisting of Si, Y and O.

Claim 31 (New): The ceramic heater according to claim 22, wherein said ceramic
substrate has
an impurity-existent area where an impurity element is locally distributed in triple
points of crystal grains, and

an impurity element-nonexistent area where an impurity is not locally distributed in the triple points of the crystal grains.

Claim 32 (New): The ceramic heater according to claim 31,
wherein said impurity element is selected from the group consisting of boron, sodium, calcium, silicon and a sintering aid.

Claim 33 (New): The ceramic heater according to claim 31,
wherein said impurity element is selected from the group consisting of Si, Y and O.

Claim 34 (New): The ceramic heater according to claim 22,
wherein said ceramic substrate comprises a nitride ceramic, a carbide ceramic or an oxide ceramic.

Claim 35 (New): The ceramic heater according to claim 22,
wherein said ceramic substrate comprises aluminum nitride or silicon carbide.

Claim 36 (New): The ceramic heater according to claim 22,
wherein said ceramic heater is capable of use at a temperature of 150°C to 200°C.

Claim 37 (New): A semiconductor producing/examining device comprising the ceramic heater claimed in Claim 22.